

# \* PATENT APPLICATION

				Page I of I
FORM PTO-1449	ATTY. DKT NO.	01-235	SER. NO.	· <del>-</del>
	APPLICANT	NAITO et al.		
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#### REFERENCE DESIGNATION

### **U.S. PATENT DOCUMENTS**

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLARGE
555		5,679,153 (Discussed on page 2 of the spec.)	Oct. 21, 1997	Dmitriev et al.		٦
STJ		6,153,165 (Corresponding to JP-A-10- 324600 which is discussed on page 2 of the spec.)	Nov. 28, 2000	Tanino et al.		
555		6,214,108 (Corresponding to JP-A- 2000-44398 which is discussed on page 2 of the spec.)	Apr. 10, 2001	Okamoto et al.		
555		6,153,166	Nov. 28, 2000	Tanino		
.535		6,203,772	Mar. 20, 2001	Tanino et al.		

### FOREIGN PATENT DOCUMENTS

	 						TRANSLA	TION
	DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO
222	JP-A-2000-34198 *	2/2/00	JAPAN				X	

\* Full English text of the JP Document will be available in machine-translated form from JP (Japanese Patent Office) English language web site at http://www1.ipdl.jpo.go.jp/PA1/cgi-bin/PA1INDEX.

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

222		Kamata et al., "Migration of shifting in epitaxial growth of thick 4H-SiC," Abstract of the  Lecture of 47 <sup>th</sup> Japan Society of Applied Physics Related Association, separate Volume 1, p.407, No. 29p-YF-6, March 2000. (Discussed on page 2 of the spec.)		
EXAMINER Rev. 10/94 (Fo	Se m 3.03	Stem 6/23/03		

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